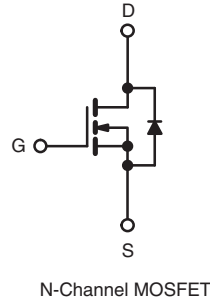
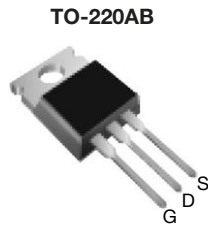




## D Series Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V) at $T_J$ max.	450	
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V	0.17
$Q_g$ max. (nC)	88	
$Q_{gs}$ (nC)	12	
$Q_{gd}$ (nC)	23	
Configuration	Single	



### FEATURES

- Optimal Design
  - Low Area Specific On-Resistance
  - Low Input Capacitance ( $C_{iss}$ )
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-of-Merit (FOM):  $R_{on} \times Q_g$
  - Fast Switching
- Compliant to RoHS Directive 2011/65/EU

### Note

\* Pb containing terminations are not RoHS compliant, exemptions may apply

### APPLICATIONS

- Consumer Electronics
  - Displays (LCD or Plasma TV)
- Lighting
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
  - Battery Chargers
- SMPS



**RoHS\***  
COMPLIANT  
HALOGEN  
**FREE**  
Available

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	SiHP25N40D-E3
Lead (Pb)-free and Halogen-free	SiHP25N40D-GE3


ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	400	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	
Gate-Source Voltage AC ( $f > 1$ Hz)		30	
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	78	
Linear Derating Factor		2.2	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	556	mJ
Maximum Power Dissipation	$P_D$	278	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	°C
Drain-Source Voltage Slope	$dV/dt$	$T_J = 125$ °C	V/ns
Reverse Diode $dV/dt^d$		0.6	
Soldering Recommendations (Peak Temperature)	for 10 s	300°	°C

### Notes

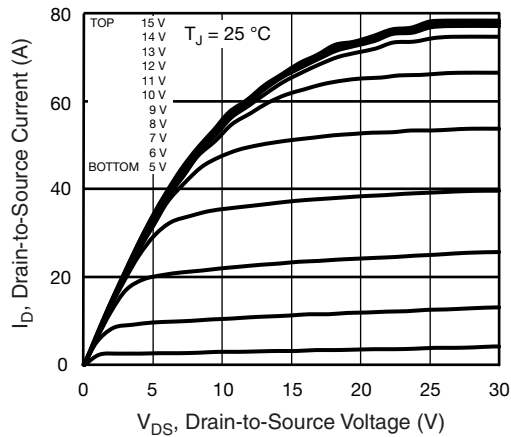
- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 2.3$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 17$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ , starting  $T_J = 25$  °C.



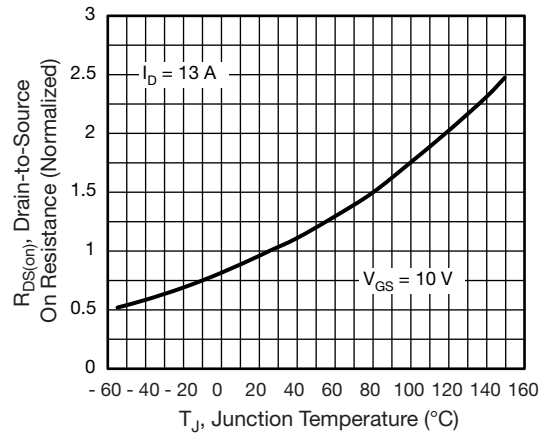
<b>THERMAL RESISTANCE RATINGS</b>				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.45	

<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		400	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 250\text{ }\mu\text{A}$		-	0.5	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		3	-	5	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 13\text{ A}$	-	0.14	0.17	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 13\text{ A}$		-	7.4	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	1707	-	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	177	-	
Reverse Transfer Capacitance	$C_{rss}$			-	19	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 13\text{ A}, V_{DS} = 320\text{ V}$	-	44	88	nC
Gate-Source Charge	$Q_{gs}$			-	12	-	
Gate-Drain Charge	$Q_{gd}$			-	23	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 320\text{ V}, I_D = 13\text{ A}, V_{GS} = 10\text{ V}, R_g = 24.6\text{ }\Omega$		-	21	42	ns
Rise Time	$t_r$			-	57	86	
Turn-Off Delay Time	$t_{d(off)}$			-	40	80	
Fall Time	$t_f$			-	37	74	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{open drain}$		-	1.8	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	24	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	78	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 13\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 13\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 20\text{ V}$		-	353	-	ns
Reverse Recovery Charge	$Q_{rr}$			-	4.4	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	24	-	A

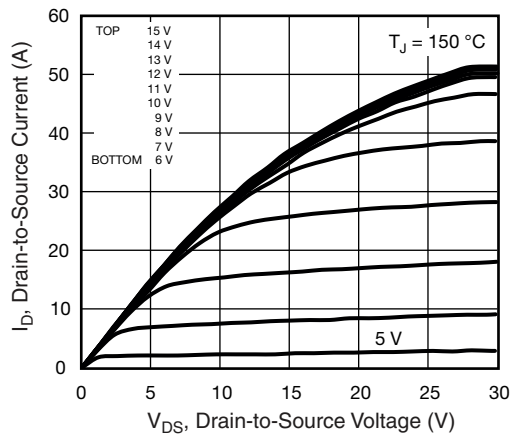
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



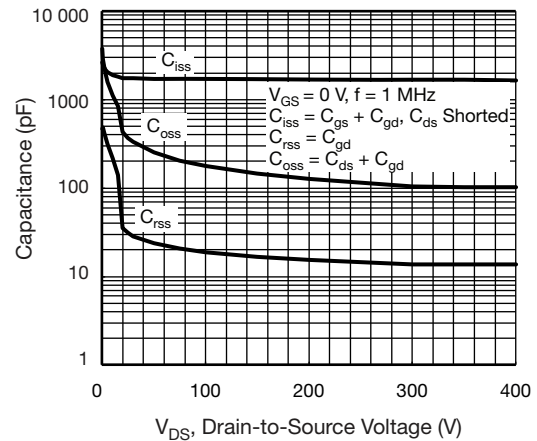
**Fig. 1 - Typical Output Characteristics**



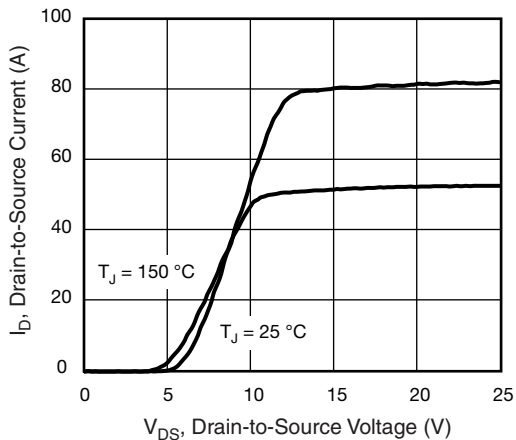
**Fig. 4 - Normalized On-Resistance vs. Temperature**



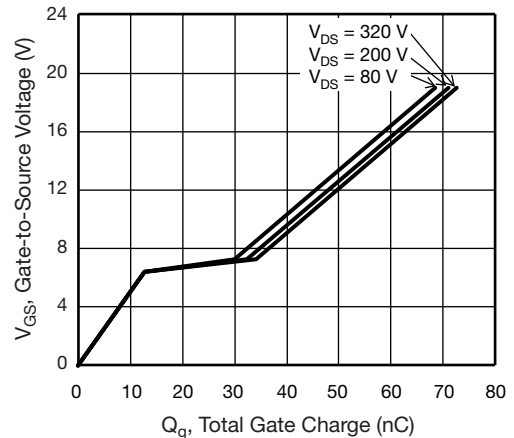
**Fig. 2 - Typical Output Characteristics**



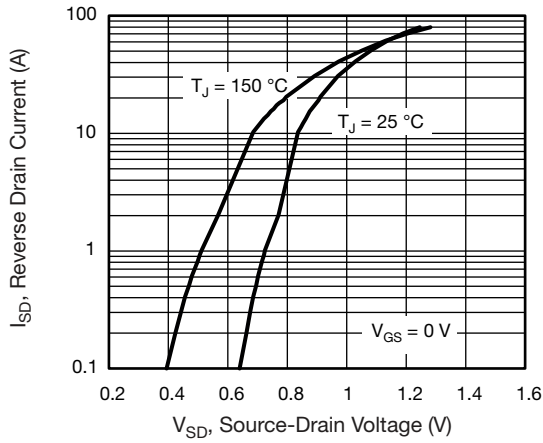
**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



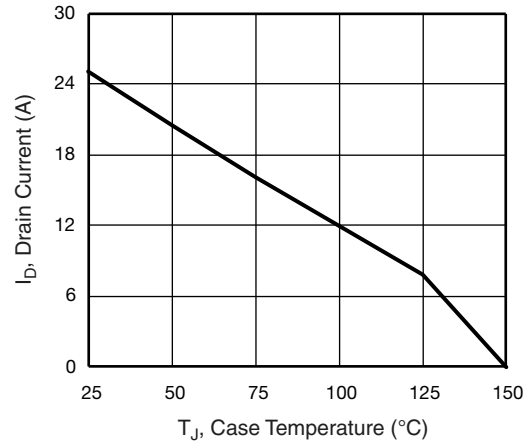
**Fig. 3 - Typical Transfer Characteristics**



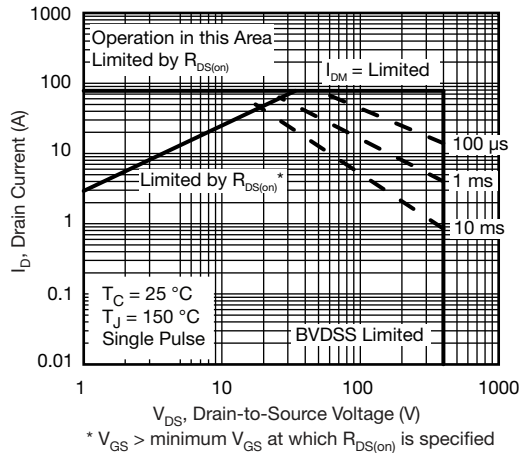
**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



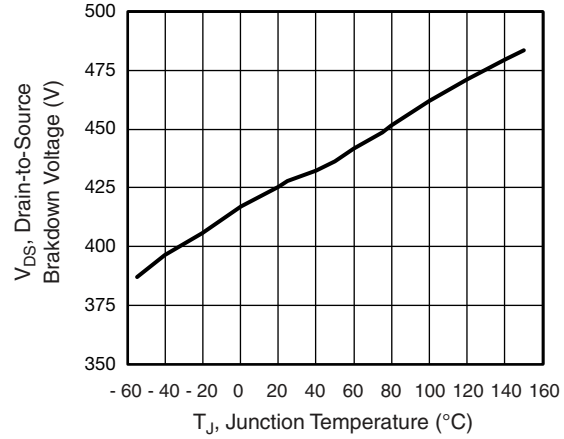
**Fig. 7 - Typical Source-Drain Diode Forward Voltage**



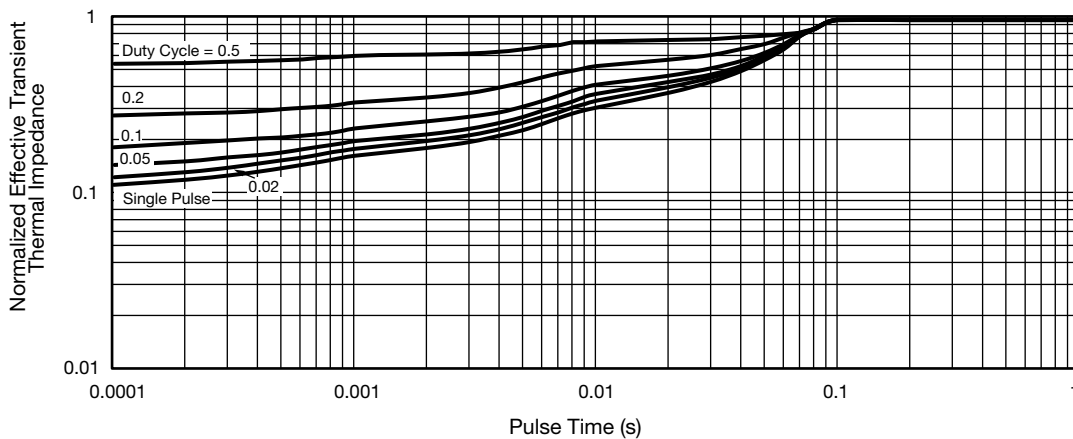
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



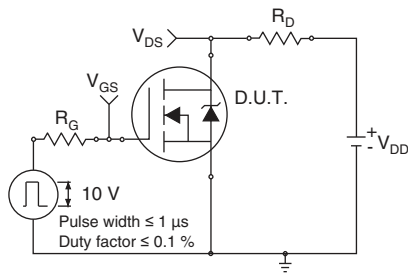
**Fig. 8 - Maximum Safe Operating Area**



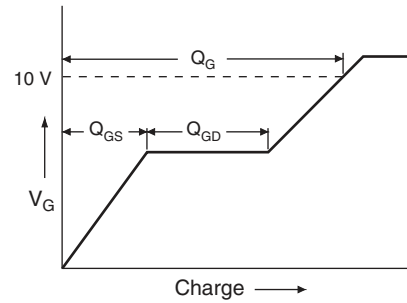
**Fig. 10 - Temperature vs. Drain-to-Source Voltage**



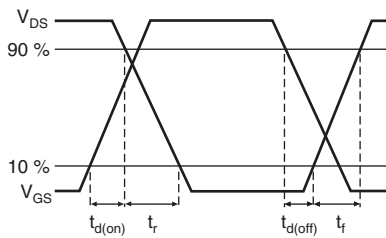
**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**



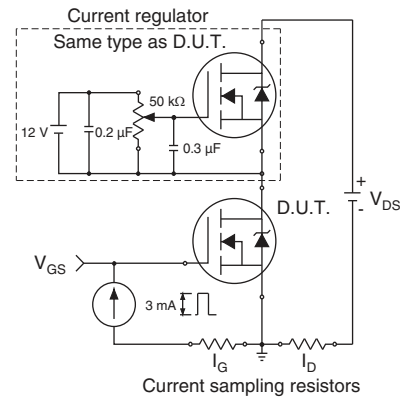
**Fig. 12 - Switching Time Test Circuit**



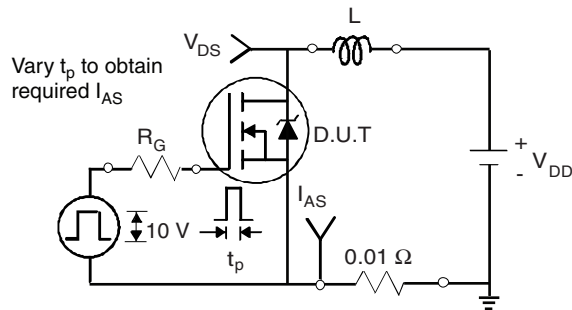
**Fig. 16 - Basic Gate Charge Waveform**



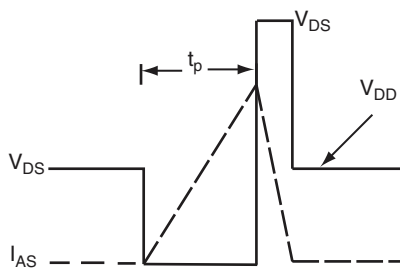
**Fig. 13 - Switching Time Waveforms**



**Fig. 17 - Gate Charge Test Circuit**

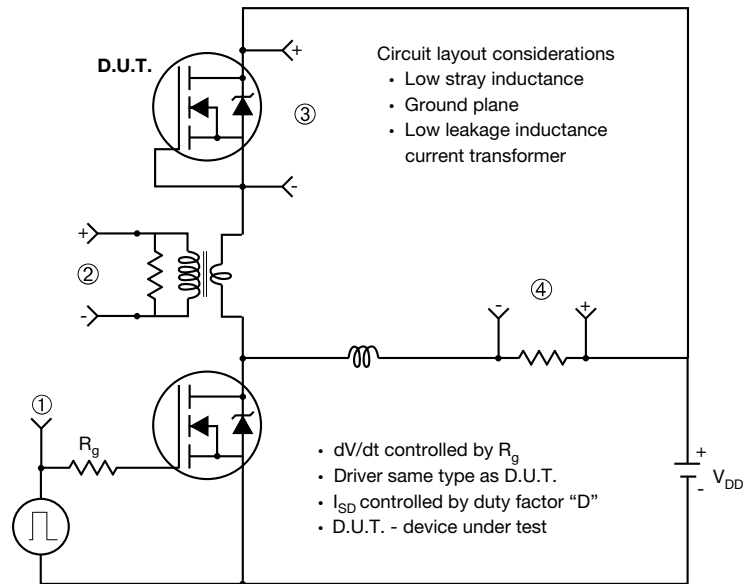


**Fig. 14 - Unclamped Inductive Test Circuit**



**Fig. 15 - Unclamped Inductive Waveforms**

### Peak Diode Recovery dV/dt Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

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